

Silicon PNP Power Transistors

2SB609

DESCRIPTION

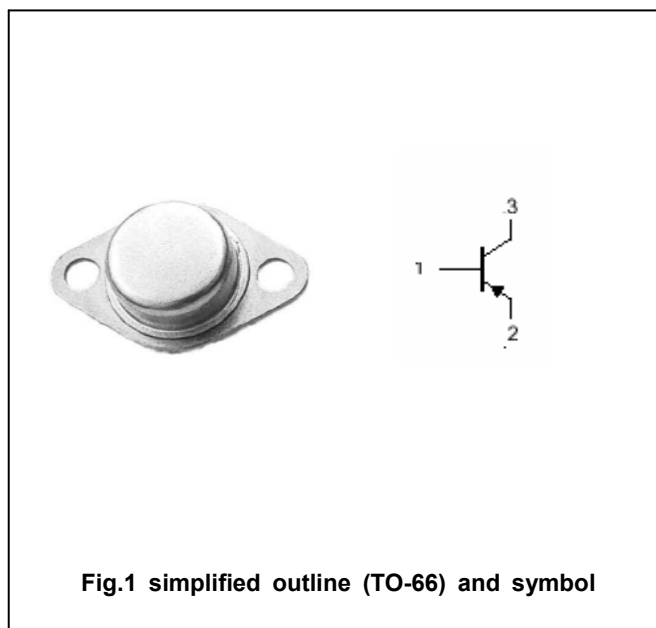
- With TO-66 package
- Wide area of safe operation

APPLICATIONS

- For use in audio frequency power amplifier application

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-4	A
P_C	Collector power dissipation	$T_C = 25 \square$	40	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-40~150	$\square$

Silicon PNP Power Transistors

2SB609

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10mA ; I_B = 0$	-80			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1mA ; I_E = 0$	-100			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -1mA ; I_C = 0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -2A ; I_B = -0.2A$			-1.0	V
V_{BE}	Base-emitter on voltage	$I_C = -0.5A ; V_{CE} = -4V$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -80V ; I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -4V ; I_C = 0$			-0.1	mA
h_{FE}	DC current gain	$I_C = -0.5A ; V_{CE} = -4V$	60		320	

Silicon PNP Power Transistors

2SB609

PACKAGE OUTLINE

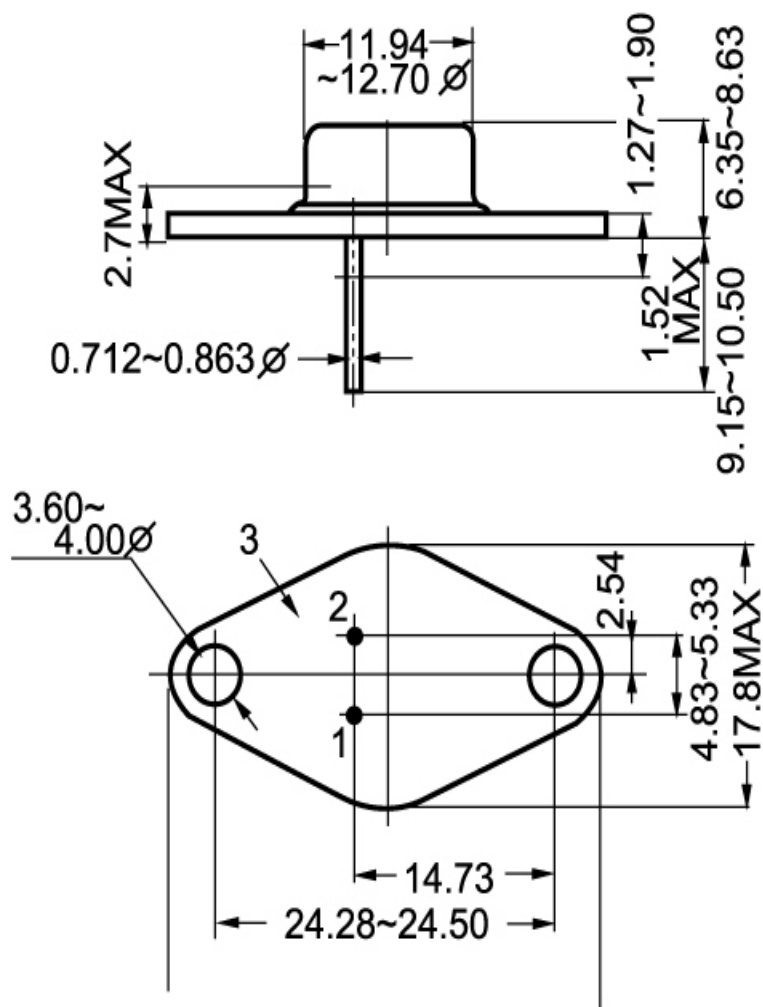


Fig.2 outline dimensions